

MOSFET - Single N-Channel

40 V, 2.1 mΩ, 150 A

NTTFS2D1N04HL

Features

- Max $R_{DS(on)}$ = 2.1 mΩ at $V_{GS} = 10$ V, $I_D = 23$ A
- Max $R_{DS(on)}$ = 3.3 mΩ at $V_{GS} = 4.5$ V, $I_D = 18$ A
- High Performance Technology for Extremely Low $R_{DS(on)}$
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- DC-DC Buck Converters
- Point of Load
- High Efficiency Load Switch and Low Side Switching
- Oring FET

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Value | Unit | | |
|---|---|--------------------------|------------------|-----|---|
| Drain-to-Source Voltage | V_{DSS} | 40 | V | | |
| Gate-to-Source Voltage | V_{GS} | ± 20 | V | | |
| Continuous Drain Current $R_{\theta JC}$ (Note 1) | Steady State | $T_C = 25^\circ\text{C}$ | I_D | 150 | A |
| | | | P_D | 83 | W |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2) | Steady State | $T_A = 25^\circ\text{C}$ | I_D | 24 | A |
| | | | P_D | 2.2 | W |
| Pulsed Drain Current | $T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$ | I_{DM} | 958 | A | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ | | |
| Source Current (Body Diode) | I_S | 69 | A | | |
| Single Pulse Drain-to-Source Avalanche Energy ($I_{AV} = 29$ A, $L = 0.3$ mH) (Note 3) | E_{AS} | 126 | mJ | | |
| Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s) | T_L | 260 | $^\circ\text{C}$ | | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Value | Unit |
|---|-----------------|-------|---------------------------|
| Junction-to-Case - Steady State (Note 1) | $R_{\theta JC}$ | 1.5 | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient - Steady State (Note 1) | $R_{\theta JA}$ | 54.8 | |

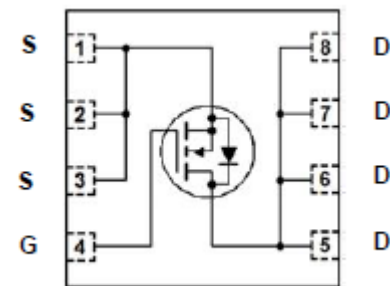
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using 1 in² pad size, 1 oz. Cu pad.
3. E_{AS} of 126 mJ is based on started $T_J = 25^\circ\text{C}$, $I_{AS} = 29$ A, $V_{DD} = 32$ V, $V_{GS} = 10$ V. 100% test at $I_{AS} = 29$ A.



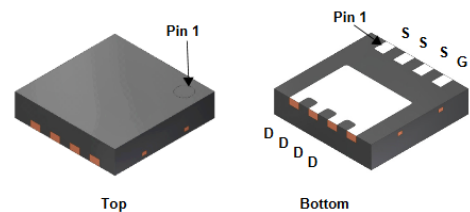
ON Semiconductor®

www.onsemi.com

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ MAX | I_D MAX |
|---------------|------------------|-----------|
| 40 V | 2.1 mΩ @ 10 V | 150 A |
| | 3.3 mΩ @ 4.5 V | |



N-CHANNEL MOSFET



WDFN8
3.3X3.3, 0.65P
CASE 483AW

ORDERING INFORMATION

| Device | Package | Shipping† |
|------------------|-----------------|--------------------|
| NTTFS2D1N04HLTWG | PQFN8 (Pb-Free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTTFS2D1N04HL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | | |
|---|--------------------------------------|--|------------------------|-------|------|-------|
| Drain-to-Source Breakdown Voltage | V _{(BR)DSS} | V _{GS} = 0 V, I _D = 250 μA | 40 | | | V |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V _{(BR)DSS} /T _J | I _D = 250 μA, ref to 25°C | | 21.80 | | mV/°C |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V, V _{DS} = 40 V | T _J = 25°C | | 10 | μA |
| | | | T _J = 125°C | | 100 | |
| Gate-to-Source Leakage Current | I _{GSS} | V _{DS} = 0 V, V _{GS} = 20 V | | | ±100 | nA |

ON CHARACTERISTICS (Note 4)

| | | | | | | |
|-----------------------------------|-------------------------------------|---|-----|-------|-----|-------|
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = 120 μA | 1.2 | | 2.0 | V |
| Threshold Temperature Coefficient | V _{GS(TH)} /T _J | I _D = 120 μA, ref to 25°C | | -4.63 | | mV/°C |
| Drain-to-Source On Resistance | R _{DS(on)} | V _{GS} = 10 V, I _D = 23 A | | 1.7 | 2.1 | mΩ |
| | | V _{GS} = 4.5 V, I _D = 18 A | | 2.5 | 3.3 | |
| Forward Transconductance | g _{FS} | V _{DS} = 15 V, I _D = 23 A | | 256 | | S |
| Gate-Resistance | R _G | T _A = 25°C | | 1 | | Ω |

CHARGES & CAPACITANCES

| | | | | | | |
|------------------------------|---------------------|--|--|------|--|----|
| Input Capacitance | C _{ISS} | V _{GS} = 0 V, f = 1 MHz, V _{DS} = 20 V | | 2745 | | pF |
| Output Capacitance | C _{OSS} | | | 645 | | |
| Reverse Transfer Capacitance | C _{RSS} | | | 38 | | |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 10 V, V _{DS} = 32 V, I _D = 11.5 A | | 43.6 | | nC |
| Total Gate Charge | Q _{G(TOT)} | V _{GS} = 4.5 V, V _{DS} = 32 V, I _D = 11.5 A | | 20.7 | | nC |
| Gate-to-Source Charge | Q _{GS} | | | 6.1 | | |
| Gate-to-Drain Charge | Q _{GD} | | | 6.2 | | |
| Plateau Voltage | V _{GP} | | | 2.5 | | |

SWITCHING CHARACTERISTICS (Note 4)

| | | | | | | |
|---------------------|---------------------|--|--|----|--|----|
| Turn-On Delay Time | t _{d(ON)} | V _{GS} = 4.5 V, V _{DD} = 32 V, I _D = 11.5 A, R _G = 2.5 Ω | | 17 | | ns |
| Rise Time | t _r | | | 12 | | |
| Turn-Off Delay Time | t _{d(OFF)} | | | 32 | | |
| Fall Time | t _f | | | 9 | | |

DRAIN-SOURCE DIODE CHARACTERISTICS

| | | | | | | | |
|-------------------------|-----------------|--|------------------------|----|------|-----|---|
| Forward Diode Voltage | V _{SD} | V _{GS} = 0 V, I _S = 23 A | T _J = 25°C | | 0.79 | 1.2 | V |
| | | | T _J = 125°C | | 0.64 | | |
| Reverse Recovery Time | t _{RR} | V _{GS} = 0 V, di _S /dt = 100 A/μs, I _S = 11.5 A | | 22 | | ns | |
| Reverse Recovery Charge | Q _{RR} | | | 17 | | nC | |
| Charge Time | t _a | V _{GS} = 0 V, di _S /dt = 100 A/μs, I _S = 11.5 A | | 22 | | ns | |
| Discharge Time | t _b | | | 13 | | ns | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Switching characteristics are independent of operating junction temperatures

5. As an N-ch device, the negative V_{gs} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

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TYPICAL CHARACTERISTICS

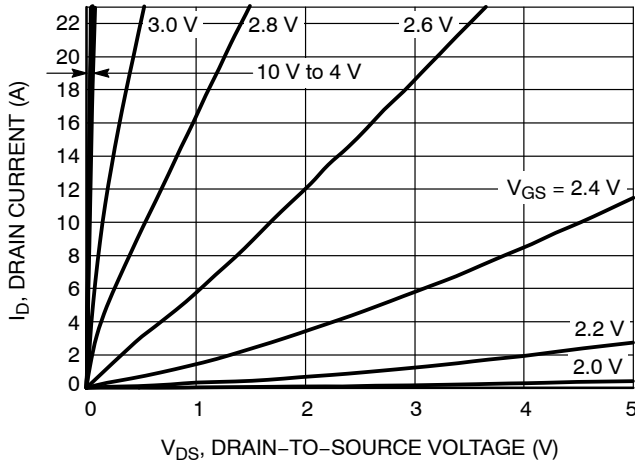


Figure 1. On-Region Characteristics

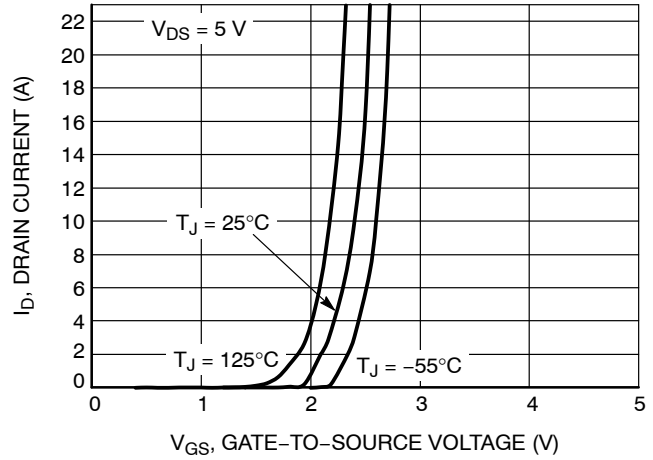


Figure 2. Transfer Characteristics

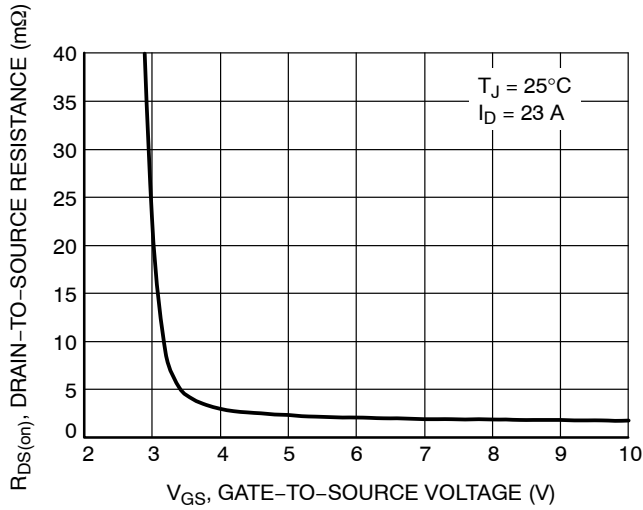


Figure 3. On-Resistance vs. Gate-to-Source Voltage

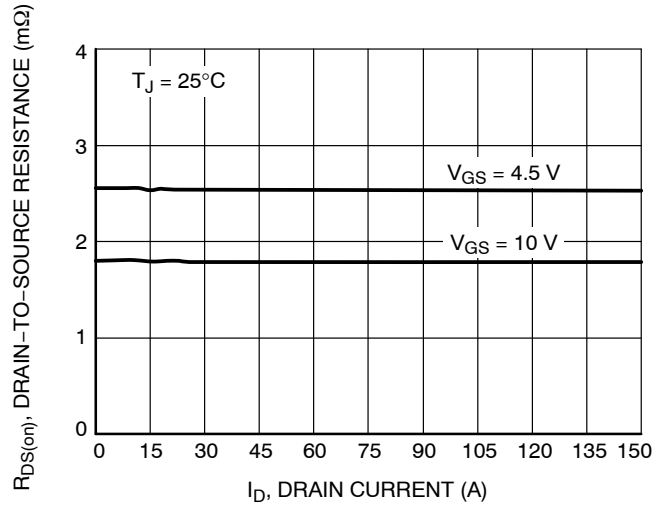


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

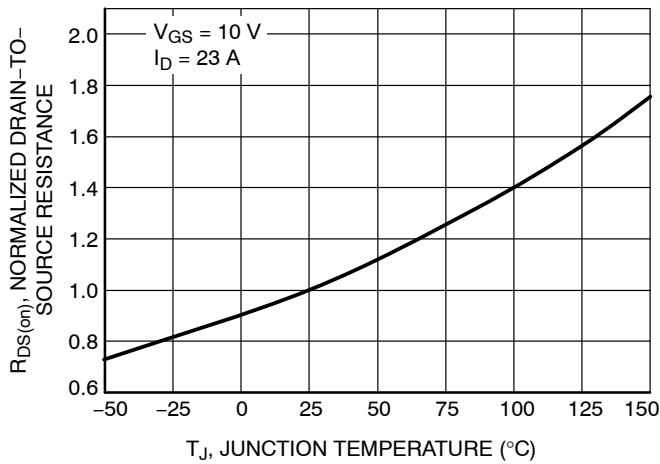


Figure 5. On-Resistance Variation with Temperature

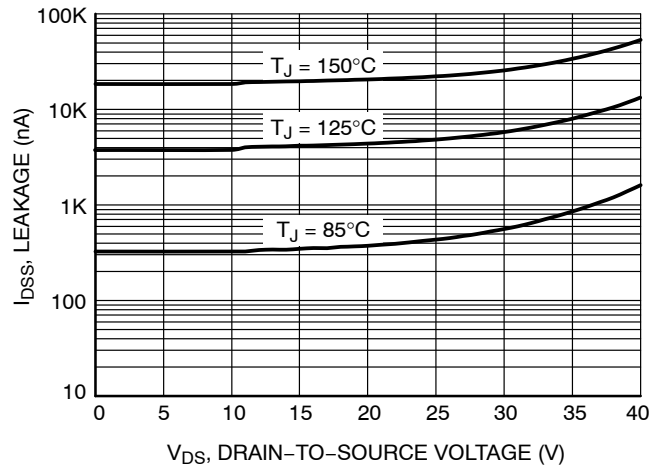


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

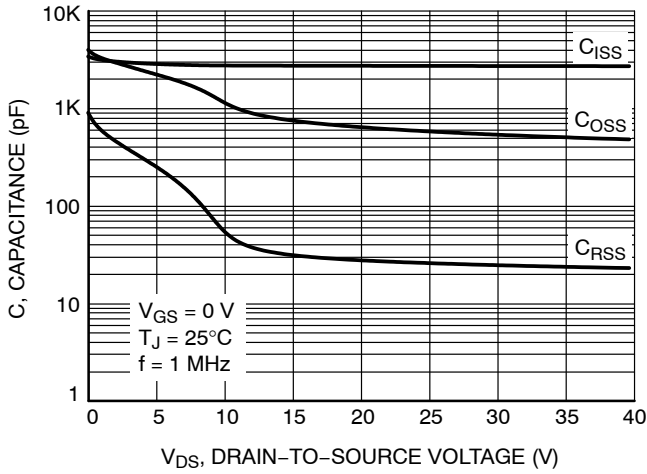


Figure 7. Capacitance Variation

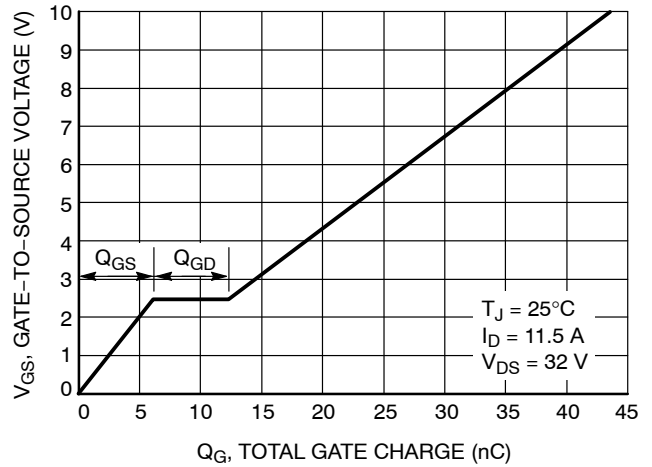


Figure 8. Gate-to-Source Voltage vs. Total Charge

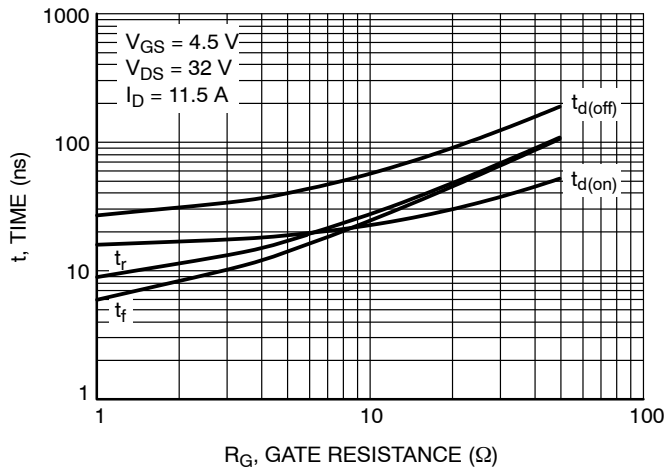


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

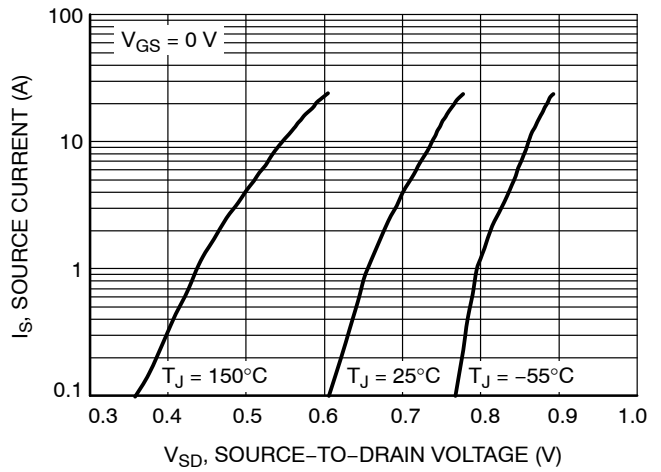


Figure 10. Diode Forward Voltage vs. Current

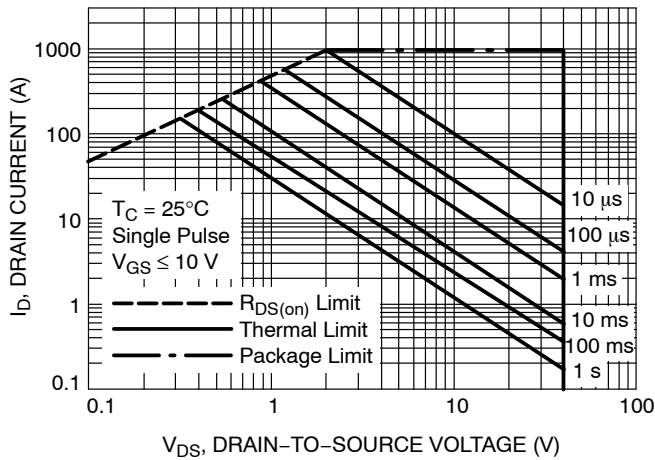


Figure 11. Maximum Rated Forward Biased Safe Operating Area

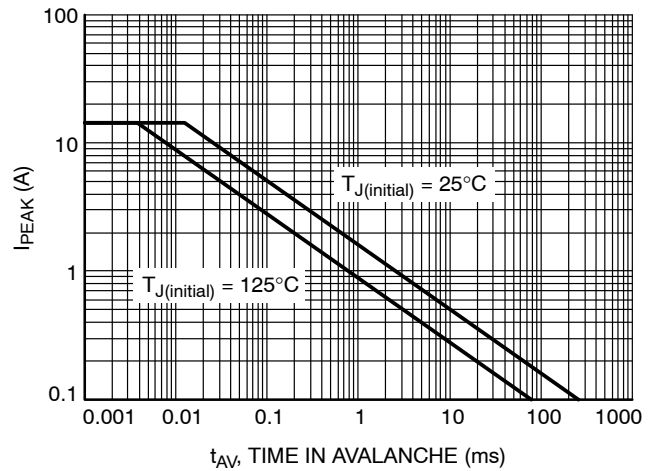


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

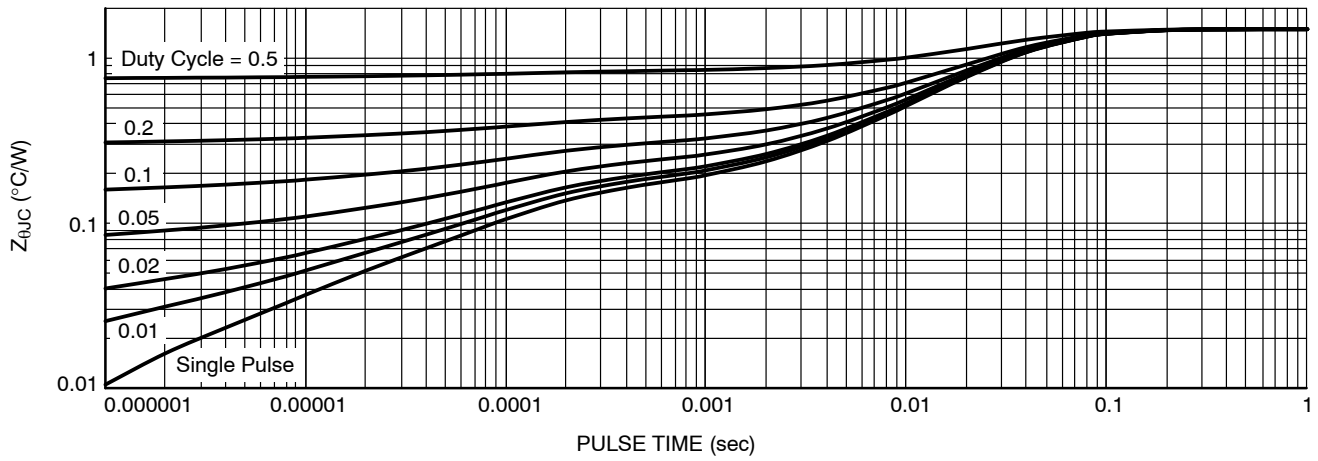
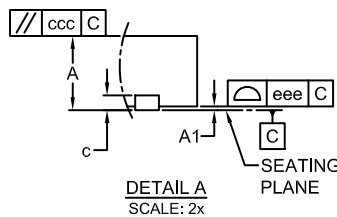
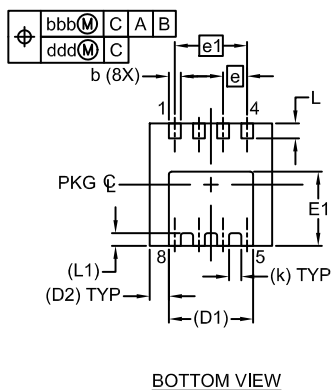
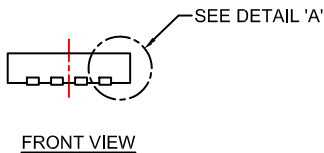
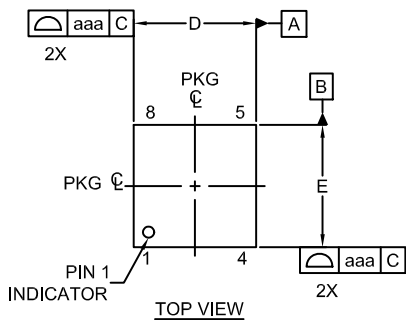


Figure 13. Transient Thermal Impedance

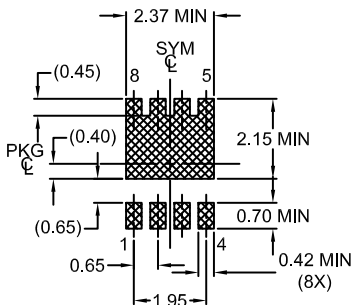
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PACKAGE DIMENSIONS

WDFN8 3.3X3.3, 0.65P
CASE 483AW
ISSUE A



LAND PATTERN RECOMMENDATION*



NOTES:

1. CONTROLLING DIMENSION: MILLIMETERS.
2. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
4. SEATING PLANE IS DEFINED BY THE TERMINALS. 'A1' IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 |
| A1 | - | - | 0.05 |
| b | 0.27 | 0.32 | 0.37 |
| c | 0.15 | 0.20 | 0.25 |
| D | 3.20 | 3.30 | 3.40 |
| D1 | 2.27 REF | | |
| D2 | 0.52 REF | | |
| E | 3.20 | 3.30 | 3.40 |
| E1 | 1.85 | 1.95 | 2.05 |
| e | 0.65 BSC | | |
| e1 | 1.95 BSC | | |
| k | 0.33 REF | | |
| L | 0.30 | 0.40 | 0.50 |
| L1 | 0.34 REF | | |
| aaa | 0.10 | | |
| bbb | 0.10 | | |
| ccc | 0.10 | | |
| ddd | 0.05 | | |
| eee | 0.05 | | |

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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